

Silicon PNP Power Transistors

2SA490

DESCRIPTION

- With TO-220 package
- Complement to type 2SC790

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

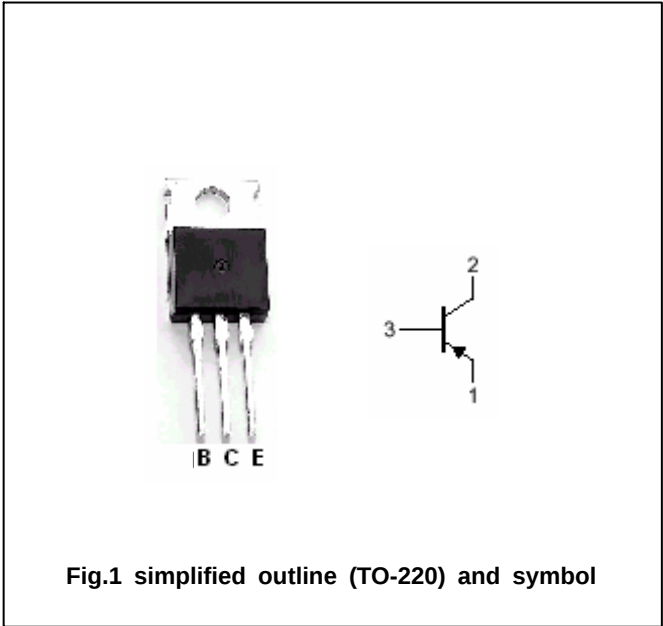


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-50	V
V _{CEO}	Collector-emitter voltage	Open base	-40	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-3	A
I _E	Emitter current		3	A
P _C	Collector power dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, I _B =0	-40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A		-0.45	-1.2	V
V _{BE}	Base-emitter voltage	I _C =-2A; V _{CE} =-2V		-0.85	-1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-2V	40		240	
h _{FE-2}	DC current gain	I _C =-2A; V _{CE} =-2V	13	50		
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		150		pF
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-2V	3			MHz

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)